

Solid State Relay OCMOS FET

# **PS7211-2A**

# 8-PIN SOP 100 V BREAK DOWN VOLTAGE 2-ch Optical Coupled MOS FET

# DESCRIPTION

The PS7211-2A is a solid state relay containing GaAs LEDs on the light emitting side (input side) and MOS FETs on the output side.

It is suitable for analog signal control because of its low offset and high linearity.

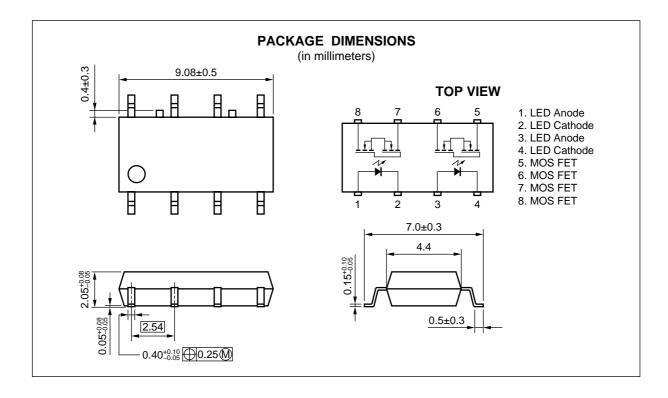
## ★ FEATURES

- 2 channel type (1 a + 1 a output)
- Low LED operating current (IF = 2 mA)
- Designed for AC/DC switching line changer
- Small and thin package (8-pin SOP, Height = 2.1 mm)
- · Low offset voltage
- Ordering number of taping product: PS7211-2A-F3, F4
- UL approved: File No. E72422 (S)
- BSI approved: No. 8241/8242
- CSA approved: No. CA 101391

#### **APPLICATIONS**

- Exchange equipment
- Measurement equipment
- FA/OA equipment

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## ★ ORDERING INFORMATION

| Part Number  | Package   | Packing Style                | Application Part Number <sup>*1</sup> |
|--------------|-----------|------------------------------|---------------------------------------|
| PS7211-2A    | 8-pin SOP | Magazine case 45 pcs         | PS7211-2A                             |
| PS7211-2A-F3 |           | Embossed Tape 1 500 pcs/reel |                                       |
| PS7211-2A-F4 |           |                              |                                       |

\*1 For the application of the Safety Standard, following part number should be used.

# ABSOLUTE MAXIMUM RATINGS (TA = 25 °C, unless otherwise specified)

| Parameter                      |  | Symbol | Ratings     | Unit    |  |
|--------------------------------|--|--------|-------------|---------|--|
| Diode                          | Forward Current (DC)                                   | lf     | 50          | mA      |  |
|                                | Reverse Voltage  | Vr     | 5.0         | V       |  |
|                                | Power Dissipation                                      | PD     | 50          | mW/ch   |  |
|                                | Peak Forward Current <sup>*1</sup>                     | IFP    | 1           | А       |  |
| MOS FET                        | MOS FET Break Down Voltage                             |        | 100         | V       |  |
|                                | Continuous Load Current                                | ١L     | 100         | mA      |  |
|                                | Pulse Load Current <sup>*2</sup><br>(AC/DC Connection) | Ilp    | 260         | mA      |  |
|                                | Power Dissipation                                      | PD     | 180         | mW/ch   |  |
| Isolation Voltage <sup>3</sup> |  | BV     | 1 500       | Vr.m.s. |  |
| Total Power Dissipation        |  | Рт     | 460         | mW      |  |
| Operating Ambient Temperature  |  | TA     | -40 to +80  | °C      |  |
| Storage Temperature            |  | Tstg   | -40 to +100 | °C      |  |

\*

\*1 PW = 100  $\mu$ s, Duty Cycle = 1 %

\*2 PW = 100 ms, 1 shot

\*3 AC voltage for 1 minute at T\_A = 25 °C, RH = 60 % between input and output

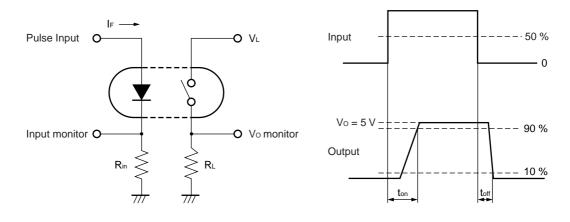
# **RECOMMENDED OPERATING CONDITIONS (TA = 25 °C)**

| Parameter             | Symbol | MIN. | TYP. | MAX. | Unit |
|-----------------------|--------|------|------|------|------|
| LED Operating Current | lF     | 2    | 10   | 20   | mA   |
| LED Off Voltage       | VF     | 0    |      | 0.5  | V    |

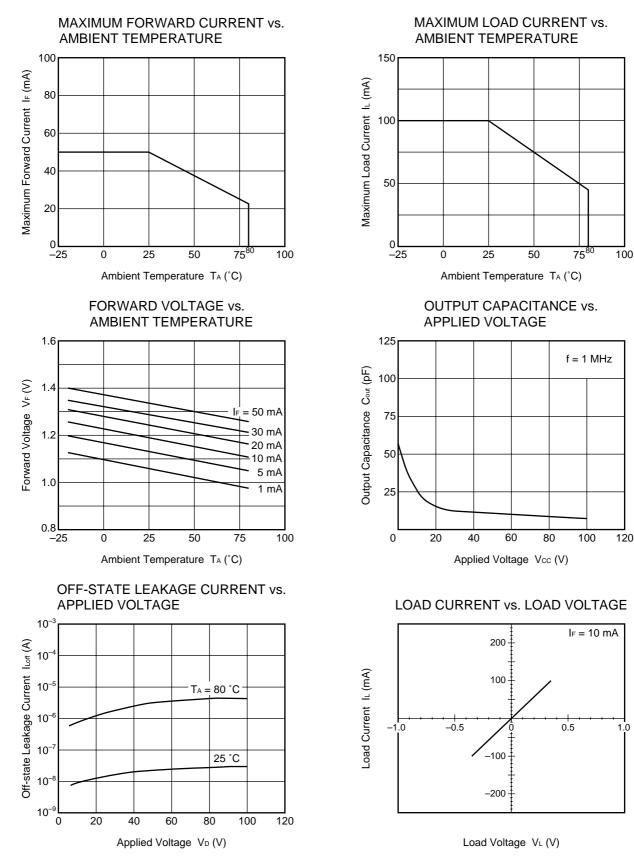
# ★ ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C)

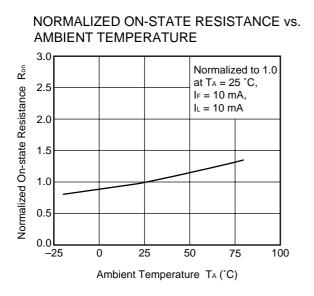
|         | Parameter                  | Symbol | Conditions                                    | MIN.            | TYP. | MAX. | Unit  |
|---------|----------------------------|--------|---|-----------------|------|------|-------|
| Diode   | Forward Voltage            | VF     | IF = 10 mA                                    |                 | 1.2  | 1.4  | V     |
|         | Reverse Current            | Ir     | V <sub>R</sub> = 5 V                          |                 |      | 5.0  | μA    |
| MOS FET | Off-state Leakage Current  | Loff   | V <sub>D</sub> = 100 V                        |                 | 0.03 | 1.0  | μA    |
|         | Output Capacitance         | Cout   | V <sub>D</sub> = 0 V, f = 1 MHz               |                 | 57   |      | pF/ch |
| Coupled | LED On-state Current       | IFon   | I∟ = 100 mA                                   |                 |      | 2.0  | mA    |
|         | On-state Resistance        | Ron1   | IF = 10 mA, IL = 10 mA                        |                 | 3.4  | 6.0  | Ω     |
|         |                            | Ron1   | $I_F$ = 10 mA, $I_L$ = 100 mA, $t \leq$ 10 ms |                 |      |      |       |
|         | Turn-on Time <sup>*1</sup> | ton    | $I_F$ = 10 mA, Vo = 5 V, PW $\geq$ 10 ms      |                 | 0.16 | 1.0  | ms    |
|         | Turn-off Time <sup>™</sup> | toff   |   |                 | 0.02 | 0.2  |       |
|         | Isolation Resistance       | Ri-o   | VI-O = 1.0 kVDC                               | 10 <sup>°</sup> |      |      | Ω     |
|         | Isolation Capacitance      | CI-0   | V = 0 V, f = 1 MHz                            |                 | 0.4  |      | pF/ch |

\*1 Test Circuit for Switching Time

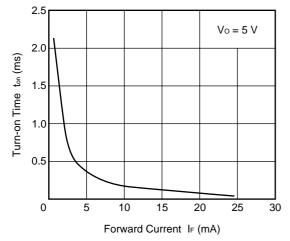


# ★ TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise specified)

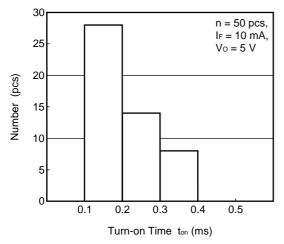




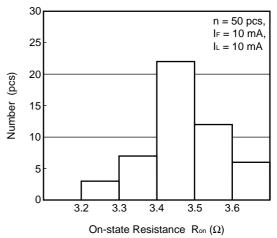
# TURN-ON TIME vs. FORWARD CURRENT



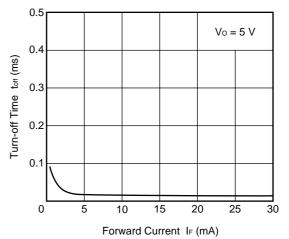
#### TURN-ON TIME DISTRIBUTION



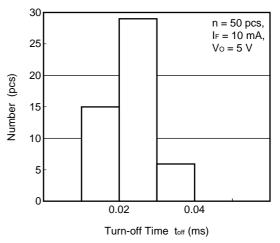
#### **ON-STATE RESISTANCE DISTRIBUTION**

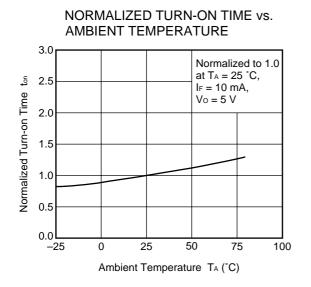


TURN-OFF TIME vs. FORWARD CURRENT

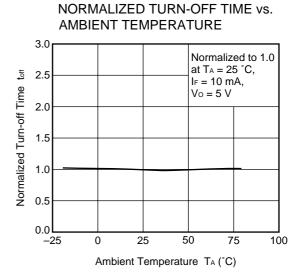


#### TURN-OFF TIME DISTRIBUTION

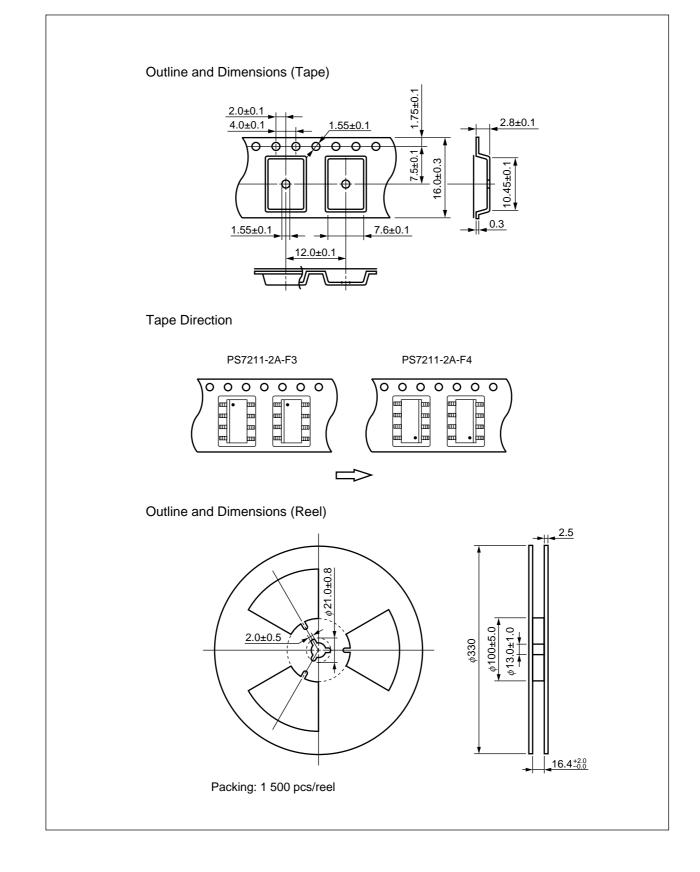




**Remark** The graphs indicate nominal characteristics.



# ★ TAPING SPECIFICATIONS (in millimeters)



# **\*** RECOMMENDED SOLDERING CONDITIONS

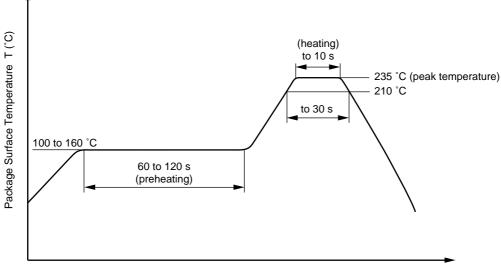
# (1) Infrared reflow soldering

- Peak reflow temperature
  235 °C (package surface temperature)
- Time of temperature higher than 210 °C
- Number of reflows
- Flux

Two Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

### Recommended Temperature Profile of Infrared Reflow

30 seconds or less





#### (2) Dip soldering

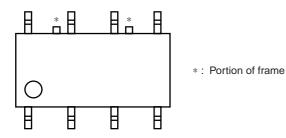
#### Temperature 260 °C or below (molten solder temperature)

- Time
- 10 seconds or less
- Number of times One
- Flux

Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

# (3) Cautions

- Fluxes
  - Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.
- Avoid shorting between portion of frame and leads.



[MEMO]

[MEMO]

# CAUTION

Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. Please do not under any circumstances break the hermetic seal.

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